

Analog IC Design

Lecture 10 Current Mirrors

Dr. Hesham A. Omran

Integrated Circuits Laboratory (ICL)
Electronics and Communications Eng. Dept.
Faculty of Engineering
Ain Shams University

Outline

1. Recapping previous key results
2. Why current source?
3. How to copy (mirror) currents?
4. Cascode current mirror
5. Wide-swing current mirror
6. Super cascode current mirror

Outline

1. Recapping previous key results
2. Why current source?
3. How to copy (mirror) currents?
4. Cascode current mirror
5. Wide-swing current mirror
6. Super cascode current mirror

MOSFET in Saturation

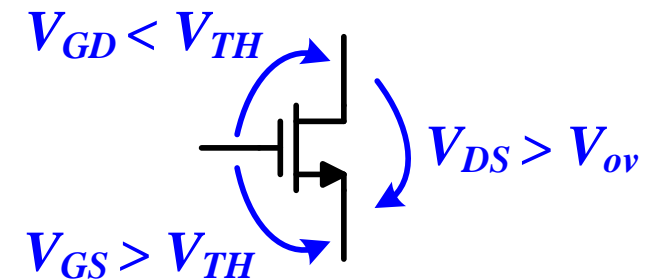
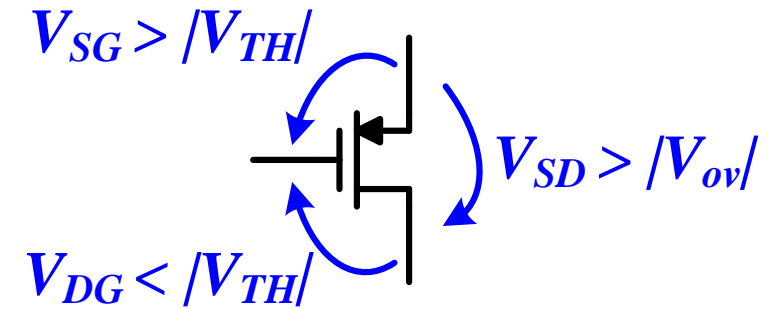
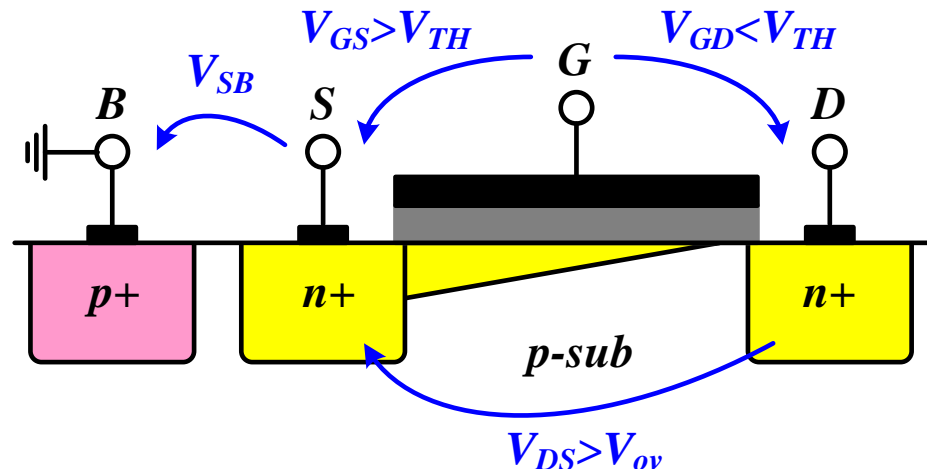
- ❑ The channel is pinched off if the difference between the gate and drain voltages is not sufficient to create an inversion layer

$$V_{GD} \leq V_{TH} \quad \text{OR} \quad V_{DS} \geq V_{ov}$$

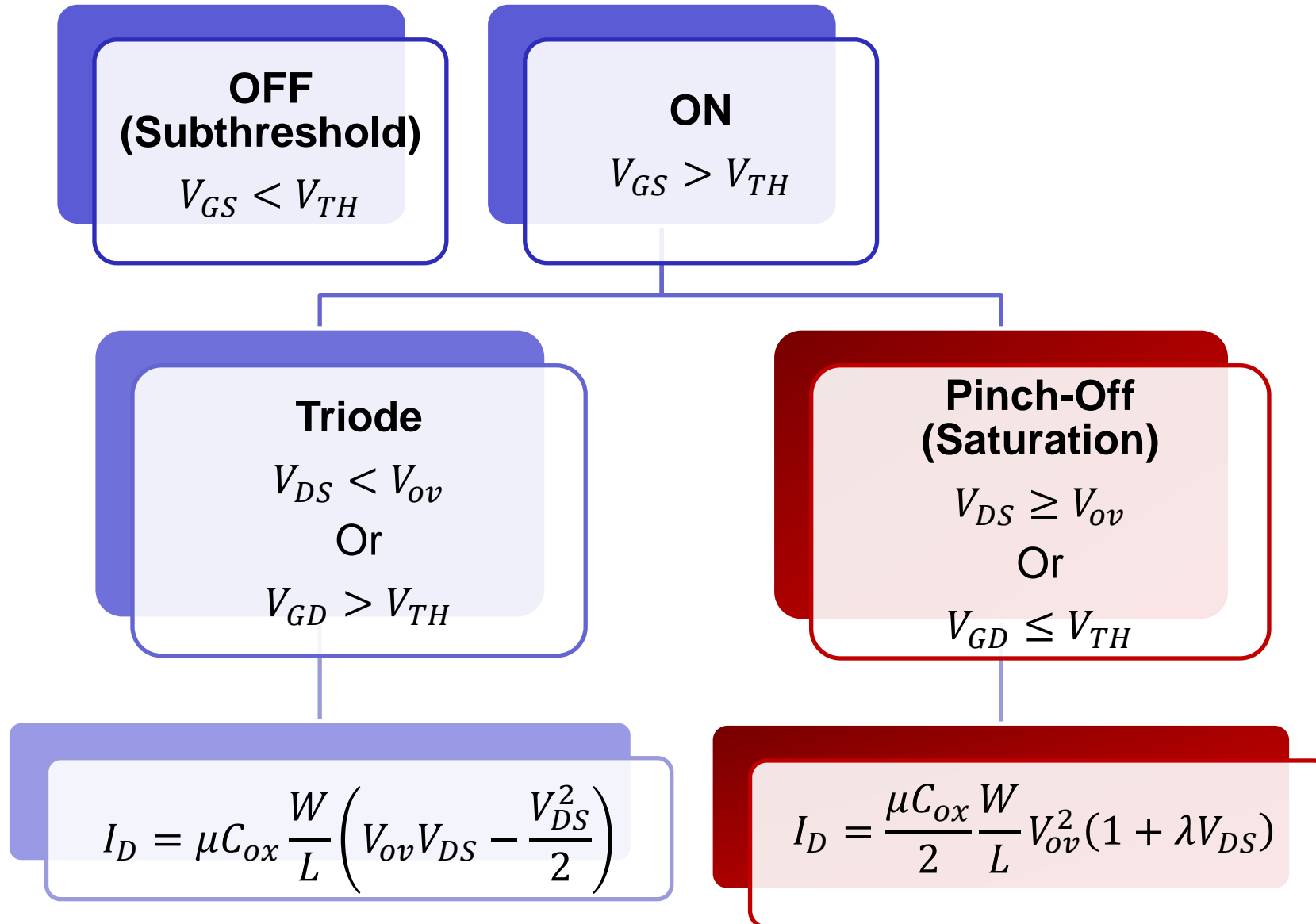
- ❑ Square-law (long channel MOS)

$$I_D = \frac{\mu_n C_{ox}}{2} \frac{W}{L} \cdot V_{ov}^2 (1 + \lambda V_{DS})$$

$$V_{SB} \uparrow \Rightarrow V_{TH} \uparrow$$



Regions of Operation Summary



High Frequency Small Signal Model

$$g_m = \frac{\partial I_D}{\partial V_{GS}} = \mu C_{ox} \frac{W}{L} V_{ov} = \sqrt{\mu C_{ox} \frac{W}{L} \cdot 2I_D} = \frac{2I_D}{V_{ov}}$$

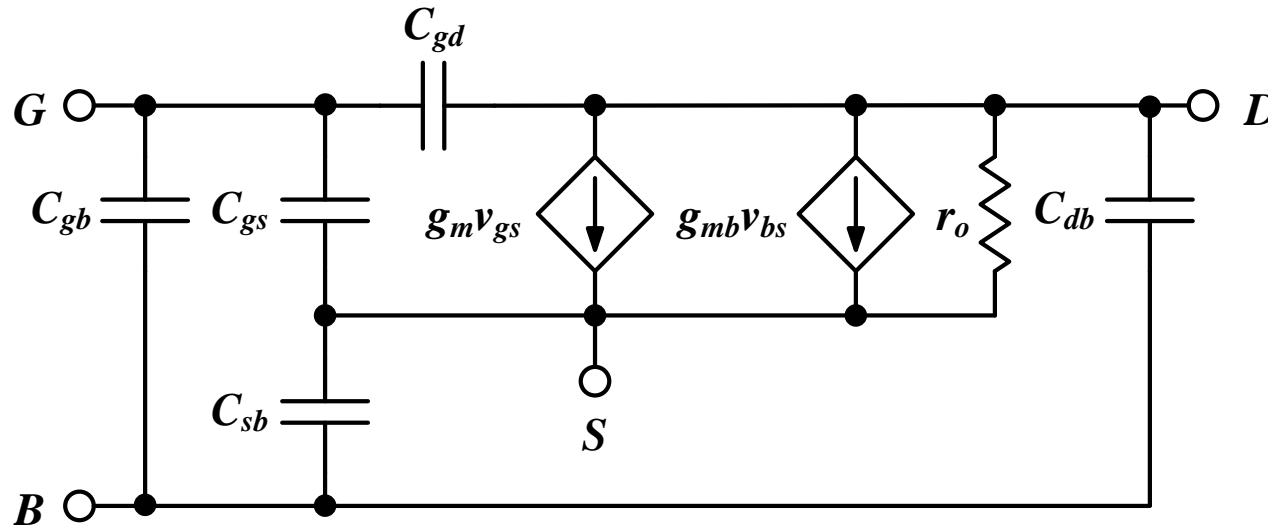
$$g_{mb} = \eta g_m \quad \eta \approx 0.1 - 0.25$$

$$r_o = \frac{1}{\partial I_D / \partial V_{DS}} = \frac{V_A}{I_D} = \frac{1}{\lambda I_D} \quad V_A \propto L \leftrightarrow \lambda \propto \frac{1}{L} \quad V_{DS} \uparrow V_A \uparrow$$

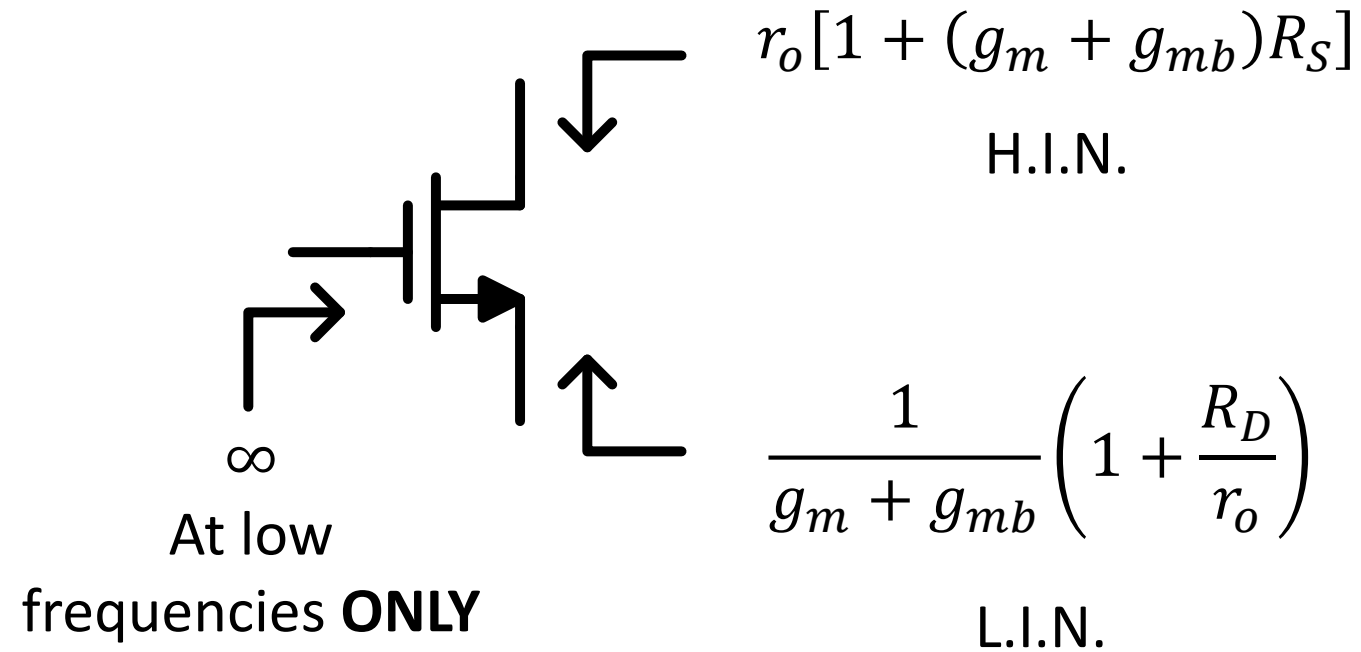
$$C_{gb} \approx 0$$

$$C_{gs} \gg C_{gd}$$

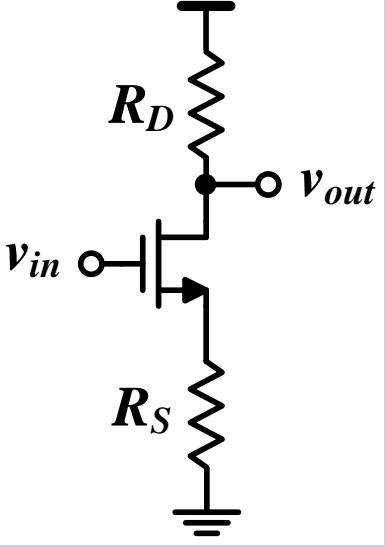
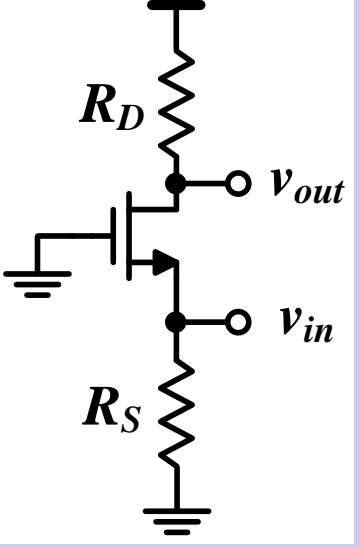
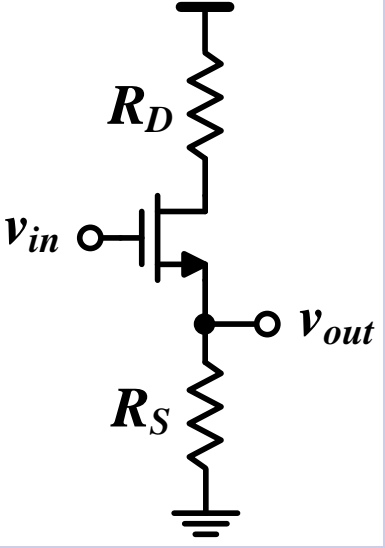
$$C_{sb} > C_{db}$$



Rin/out Shortcuts Summary



Summary of Basic Topologies

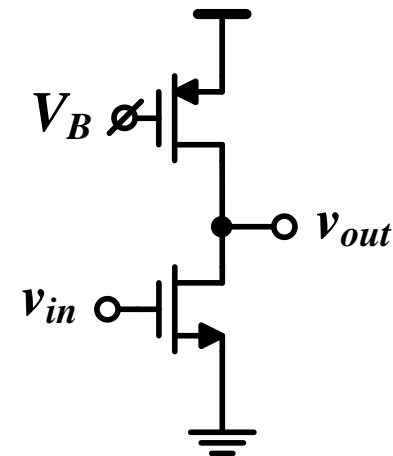
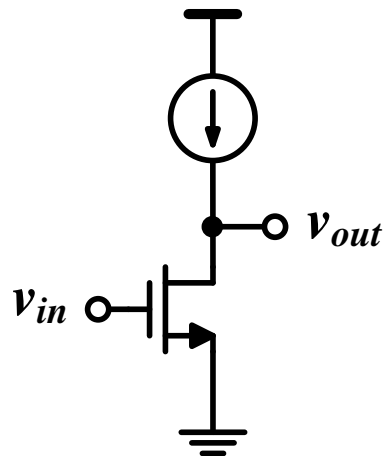
	CS	CG	CD (SF)
			
	Voltage & current amplifier	Voltage amplifier Current buffer	Voltage buffer Current amplifier
R_{in}	∞	$R_S \parallel \frac{1}{g_m + g_{mb}} \left(1 + \frac{R_D}{r_o} \right)$	∞
R_{out}	$R_D \parallel r_o [1 + (g_m + g_{mb})R_S]$	$R_D \parallel r_o$	$R_S \parallel \frac{1}{g_m + g_{mb}} \left(1 + \frac{R_D}{r_o} \right)$
G_m	$\frac{-g_m}{1 + (g_m + g_{mb})R_S}$	$g_m + g_{mb}$	$\frac{g_m}{1 + R_D/r_o}$

Outline

1. Recapping previous key results
2. Why current source?
3. How to copy (mirror) currents?
4. Cascode current mirror
5. Wide-swing current mirror
6. Super cascode current mirror

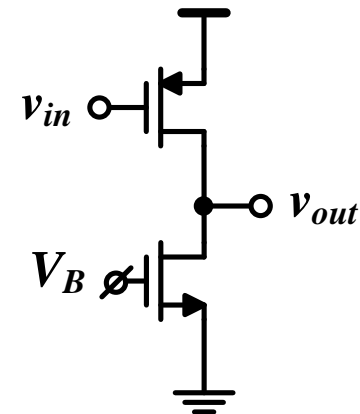
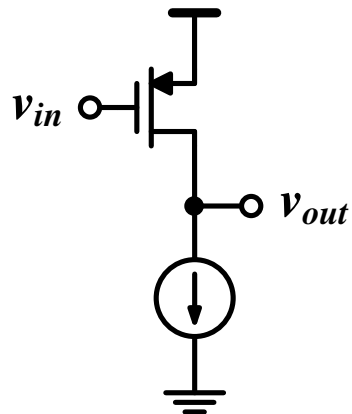
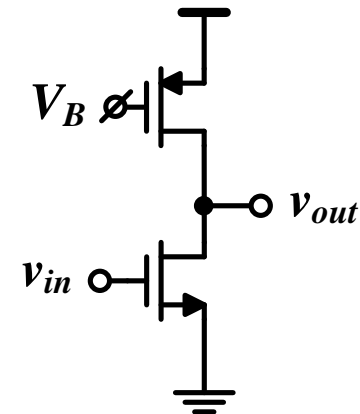
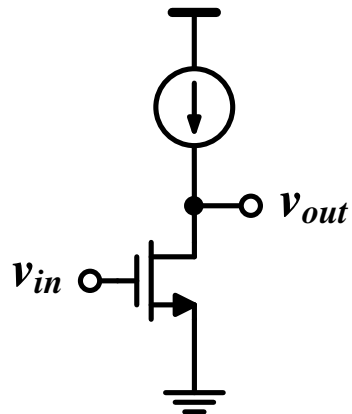
Why Current Source?

- ❑ A current source is an ideal load
 - Sets DC bias point accurately
 - Infinite R_{out} (ac o.c.)
 - No DC voltage drop
 - Small chip area
- ❑ Simply, a large resistor without the large resistor drawbacks
- ❑ The current source is practically implemented using a MOSFET
 - Finite $R_{out} = r_o$ and subtracts V_{ov} from voltage headroom



Sink and Source Currents

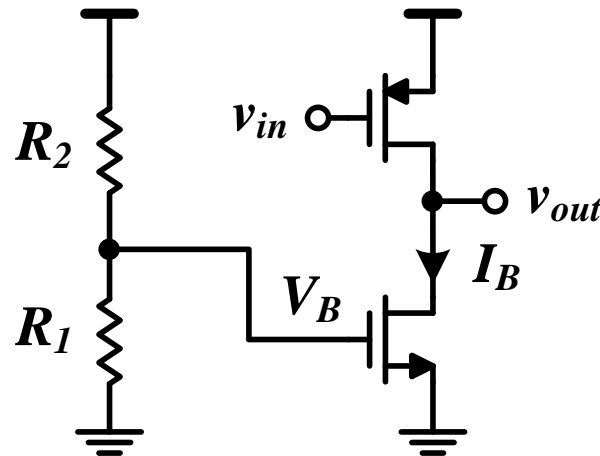
- ❑ Use PMOS to source current (from VDD)
- ❑ Use NMOS to sink current (to GND)



BAD Current Source

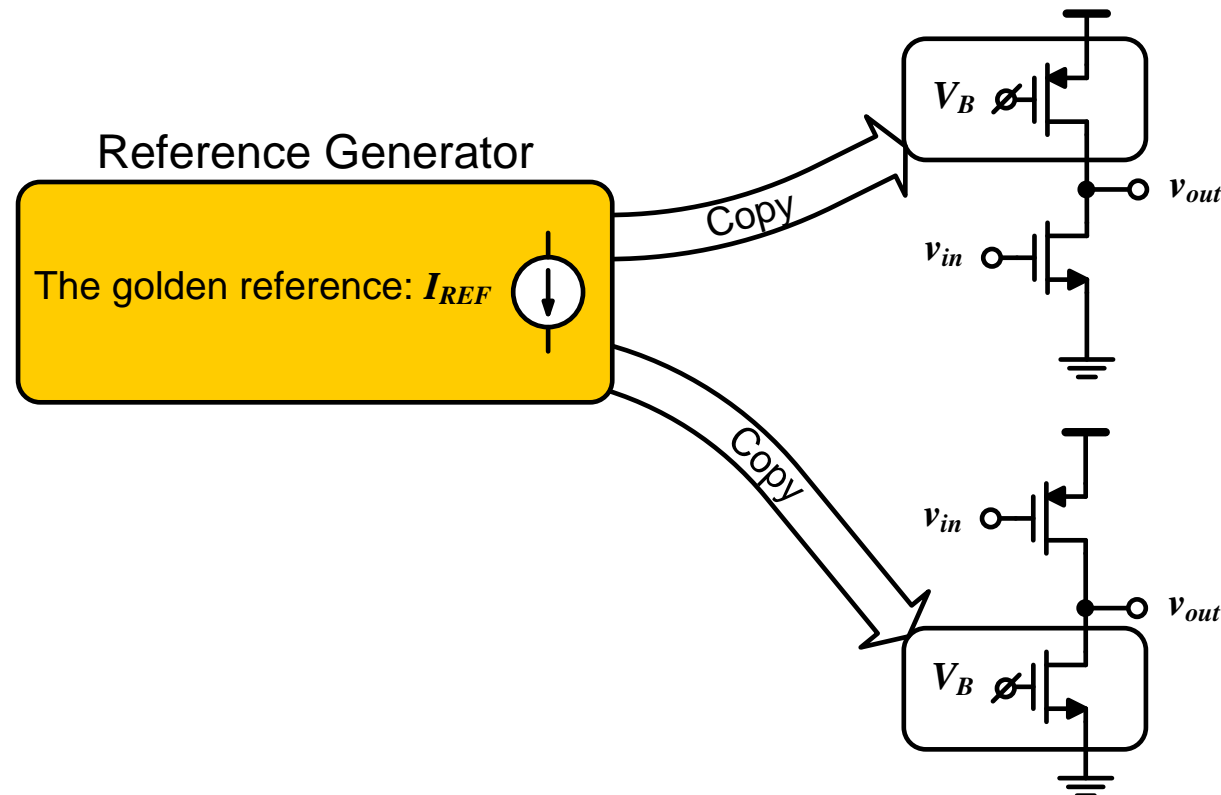
$$I_B \approx \frac{\mu C_{ox}}{2} \frac{W}{L} (V_B - V_{TH})^2 = \frac{\mu C_{ox}}{2} \frac{W}{L} \left(\frac{R_1}{R_1 + R_2} V_{DD} - V_{TH} \right)^2$$

- ❑ Sensitive to PVT (process, voltage, and temperature) variations
 - P: V_{TH} may vary $\pm 50 \text{ mV}$
 - V: V_{DD} may vary $\pm 10\%$
 - T: μ varies a lot with temperature
- ❑ Even if V_B is stable, I_B will not be stable



How to Generate Robust Currents?

- ❑ The golden reference (I_{REF}) is designed to be PVT insensitive
 - I_{REF} is generated using a relatively complicated reference circuit
 - We cannot make a reference circuit for every biasing branch!
 - Solution: Make copies of I_{REF} .

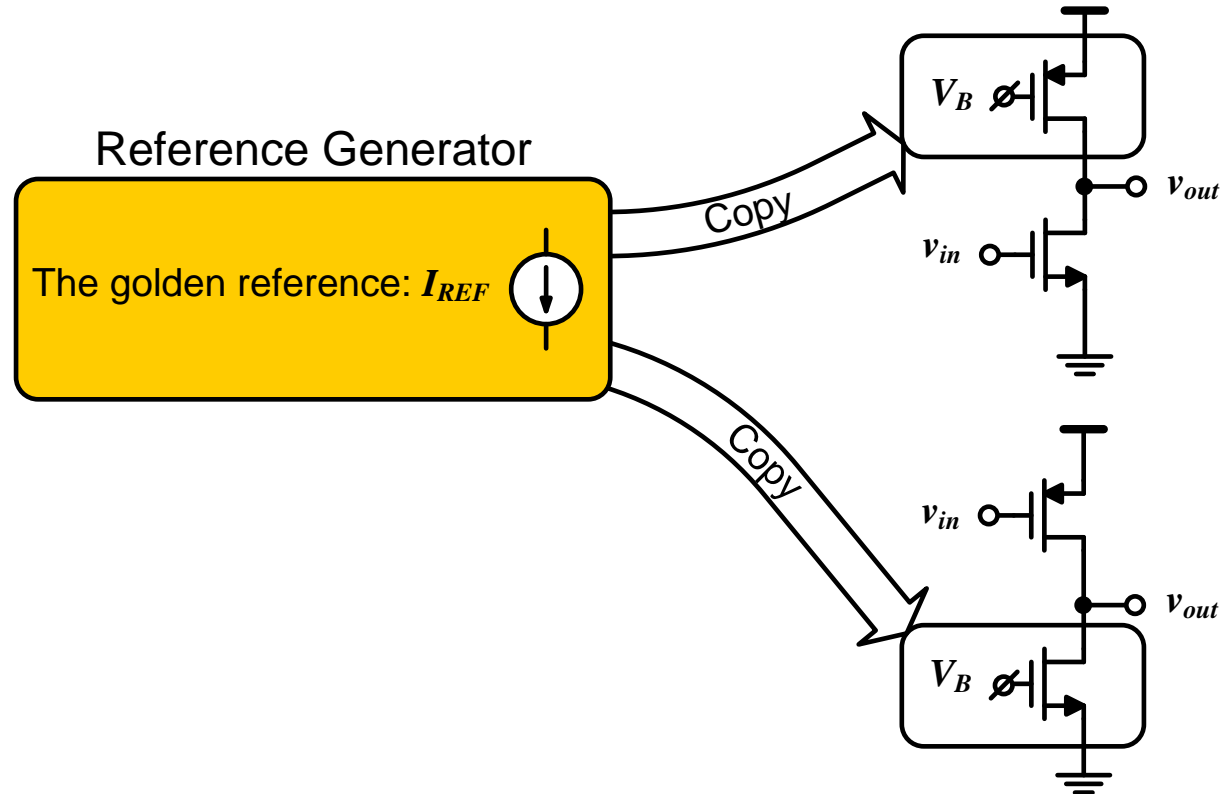


Outline

1. Recapping previous key results
2. Why current source?
3. How to copy (mirror) currents?
4. Cascode current mirror
5. Wide-swing current mirror
6. Super cascode current mirror

How to Copy (Mirror) Currents?

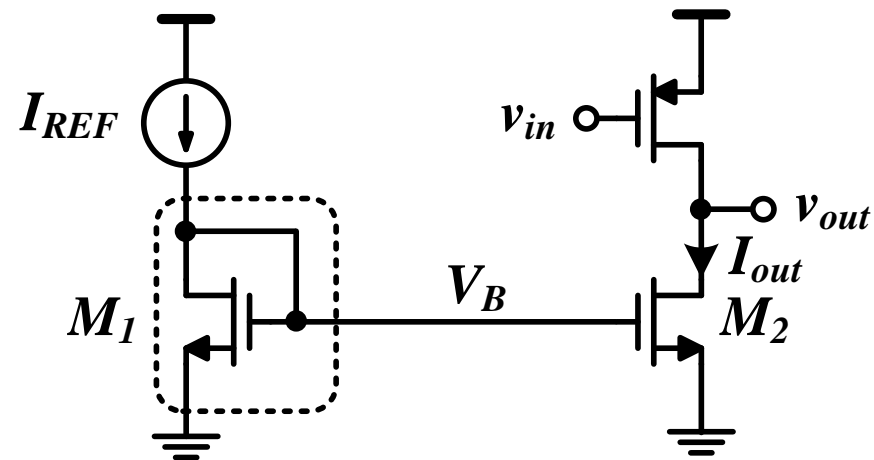
- ❑ We normally use the transistor to convert V to I
- ❑ We now need to convert I to V : convert I_{REF} to V_B
 - How to convert I to V ?



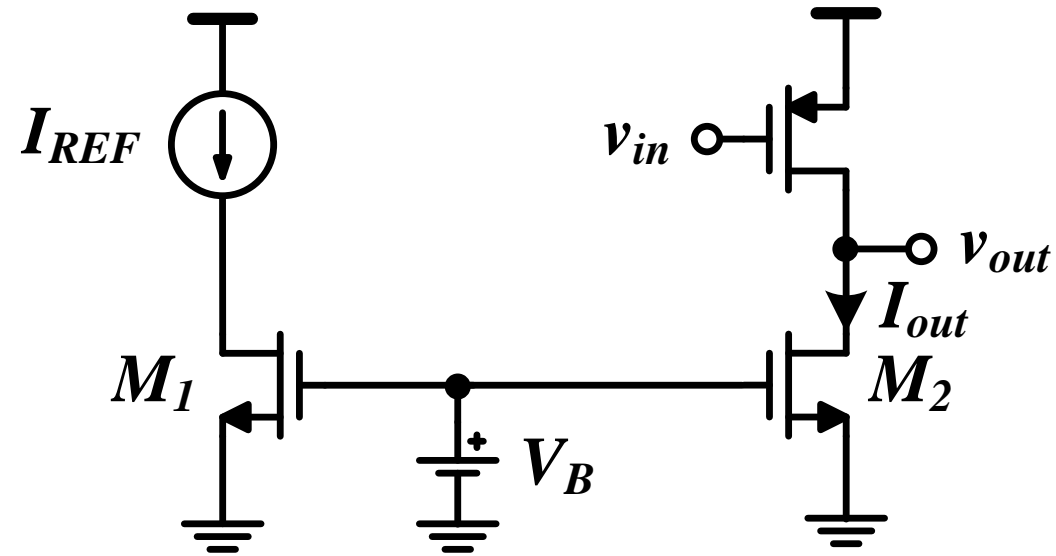
How to Copy (Mirror) Currents?

- ❑ We can convert I to V using a diode connected transistor (M1).
- ❑ M2 converts V back to I .
- ❑ M1 and M2 have the same V_{GS} and both work in saturation.
 - They will have the same current (if they are MATCHED).
- ❑ If sizing is different, we can scale I_{REF} up or down.
- ❑ I_{out} is **insensitive** to PVT variations.
 - But V_B may change due to PVT variations.

$$\frac{I_{out}}{I_{REF}} = \frac{\frac{\mu C_{ox}}{2} \left(\frac{W}{L}\right)_2 (V_B - V_{TH})^2}{\frac{\mu C_{ox}}{2} \left(\frac{W}{L}\right)_1 (V_B - V_{TH})^2} = \left(\frac{W}{L}\right)_2 \left(\frac{W}{L}\right)_1^{-1}$$

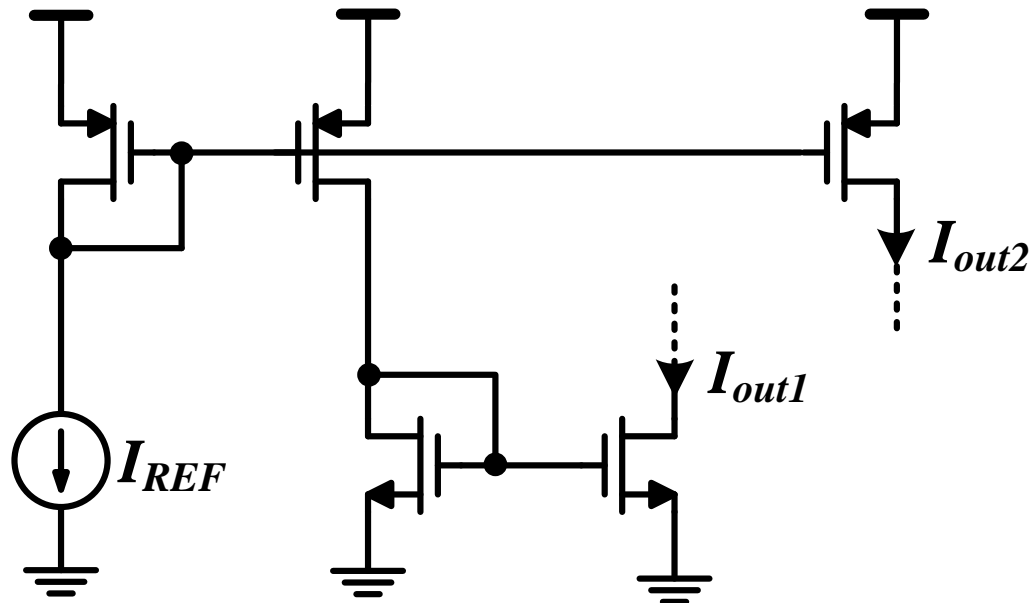


Is This a Current Mirror?



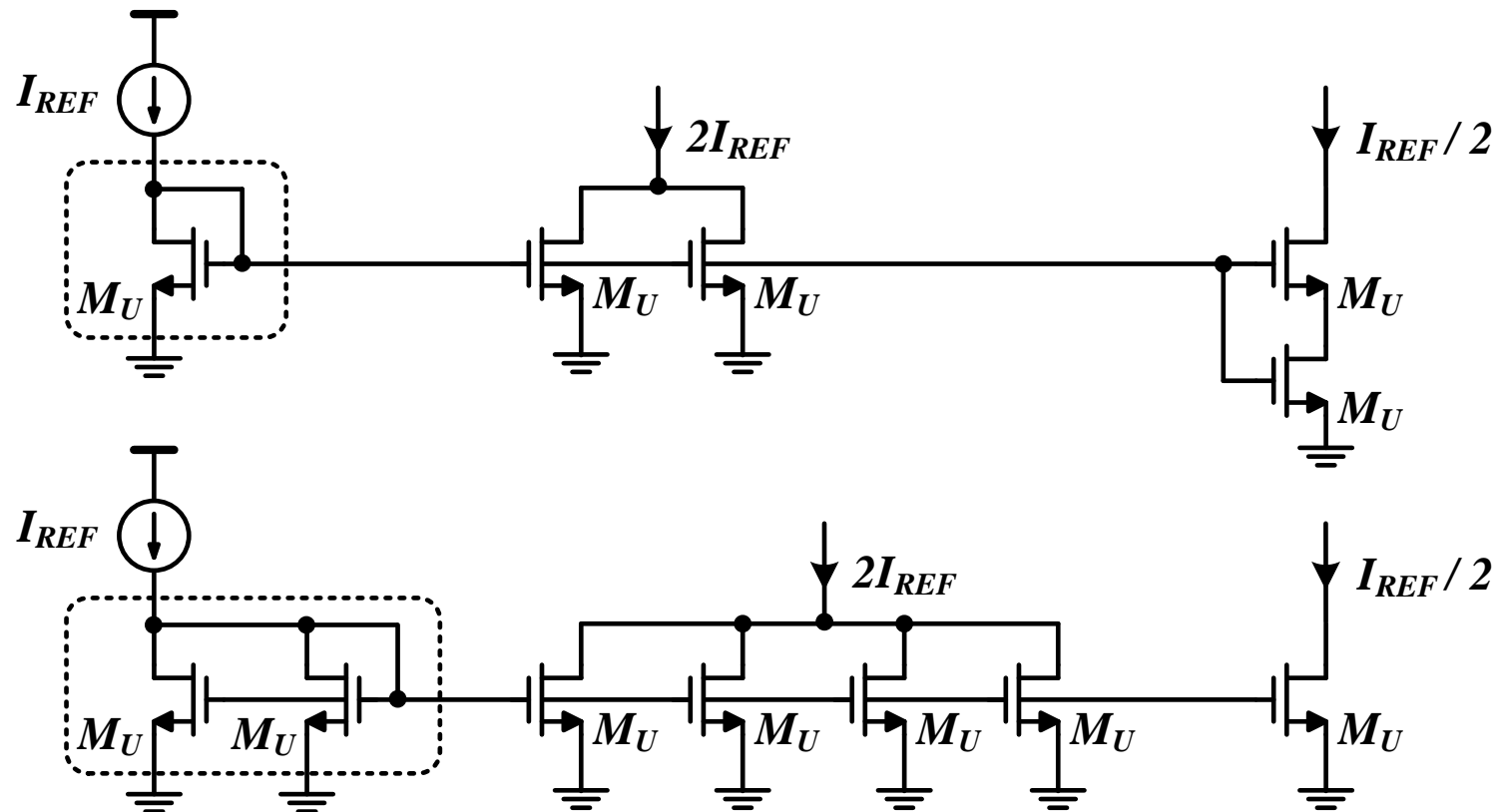
Sink and Source Currents

- ❑ Use PMOS mirror to source current (from VDD)
- ❑ Use NMOS mirror to sink current (to GND)



Scale Current Up and Down

- ❑ Currents can be scaled up or down by connecting unit transistors in parallel (accurate) or series (not as accurate: why?)
- ❑ ALWAYS use matched unit transistors (same L , W , orientation, etc.)



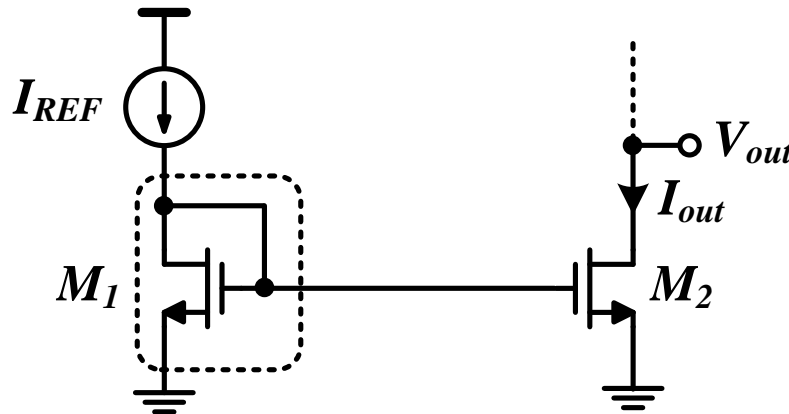
V_{DS} Dependence

□ Dependence of I_D on V_{DS} introduces two types of errors

1. M2 has finite $R_{out} = \frac{\Delta V_{out}}{\Delta I_{out}} \rightarrow$ If V_{out} varies, I_{out} will vary
2. Even if V_{out} does not vary: $V_{DS1} \neq V_{DS2}$

□ We usually scale W (unit transistors) and keep L equal: $\lambda_1 \approx \lambda_2$

$$\frac{I_{out}}{I_{REF}} = \frac{\frac{\mu C_{ox}}{2} \left(\frac{W}{L}\right)_2 (V_B - V_{TH})^2 (1 + \lambda_2 V_{DS2})}{\frac{\mu C_{ox}}{2} \left(\frac{W}{L}\right)_1 (V_B - V_{TH})^2 (1 + \lambda_1 V_{DS1})} = \left(\frac{W}{L}\right)_2 \frac{(1 + \lambda_2 V_{DS2})}{(1 + \lambda_1 V_{DS1})}$$

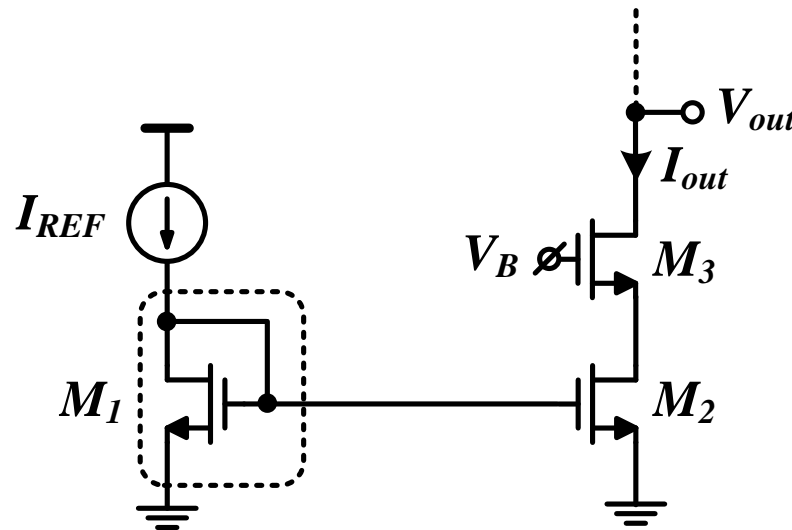


Outline

1. Recapping previous key results
2. Why current source?
3. How to copy (mirror) currents?
4. Cascode current mirror
5. Wide-swing current mirror
6. Super cascode current mirror

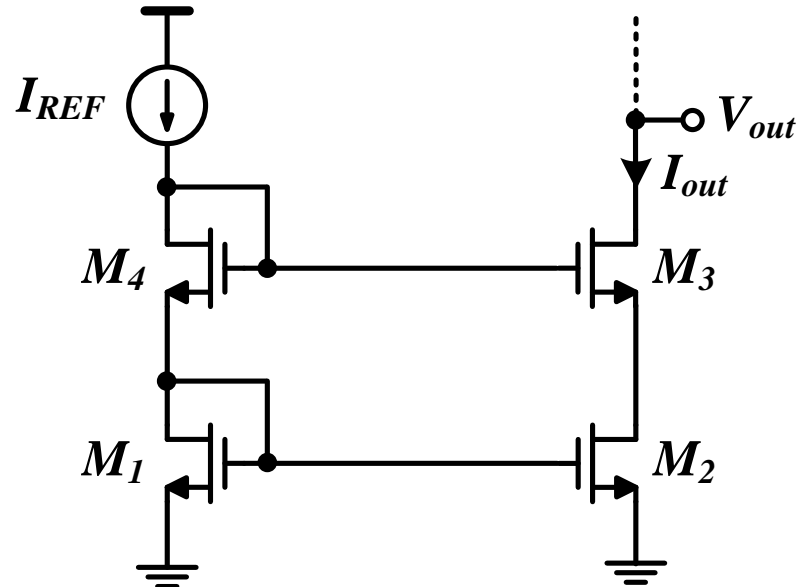
Cascode Current Mirror (1)

- ❑ R_{out} can be boosted by using cascode
 - Reduced $\Delta I_{out} = \frac{\Delta V_{out}}{R_{out}}$ for a given ΔV_{out}
- ❑ But still $V_{DS1} \neq V_{DS2} \rightarrow$ still have static error in the mirroring ratio
 - Set $V_B = V_{GS3} + V_{GS1} \rightarrow V_{DS2} = V_{DS1} = V_{GS1}$
- ❑ How to generate V_B ?



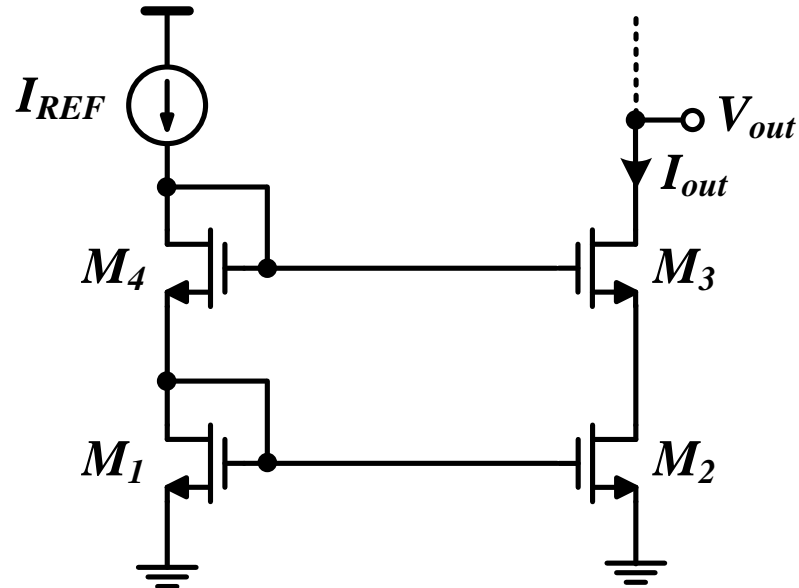
Cascode Current Mirror (2)

- ❑ M3 and M4 have the same V_{GS} .
 - Thus M1 and M2 will have the same V_{DS} .
- ❑ Note that the mirroring action is performed by M1 and M2 only.
 - The role of M3 and M4 is to guarantee $V_{DS1} = V_{DS2}$.
- ❑ If both V_{GS} and V_{DS} are equal, current will be perfectly mirrored.
 - Actually even if the transistors are not in saturation!



Quiz

- ☐ Compliance range: V_{out} range where the CS behaves as a CS
- ☐ Assume $V_{TH1,2} = 0.4V$, $V_{TH3,4} = 0.45V$ (body effect), $V_{ov} = 0.1V$.
- ☐ Calculate the CS compliance range.

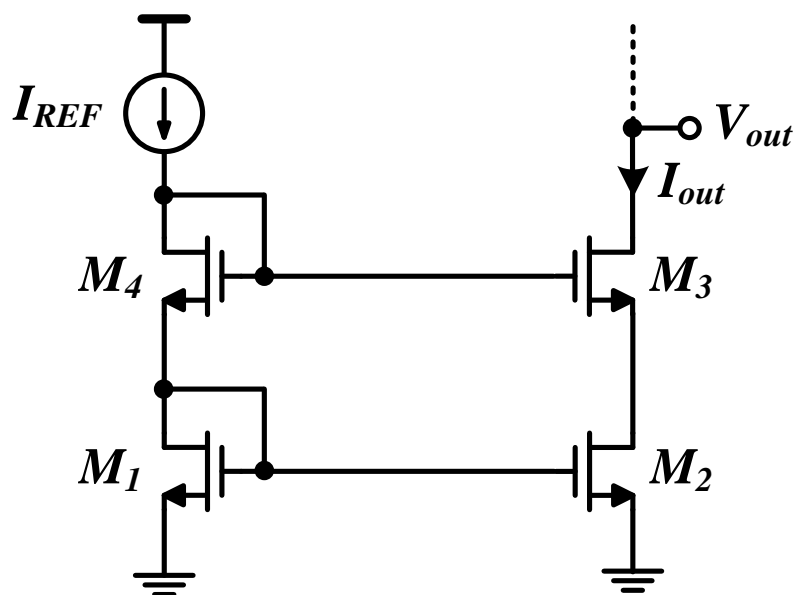


Outline

1. Recapping previous key results
2. Why current source?
3. How to copy (mirror) currents?
4. Cascode current mirror
5. Wide-swing current mirror
6. Super cascode current mirror

Cascode CM Wastes Headroom

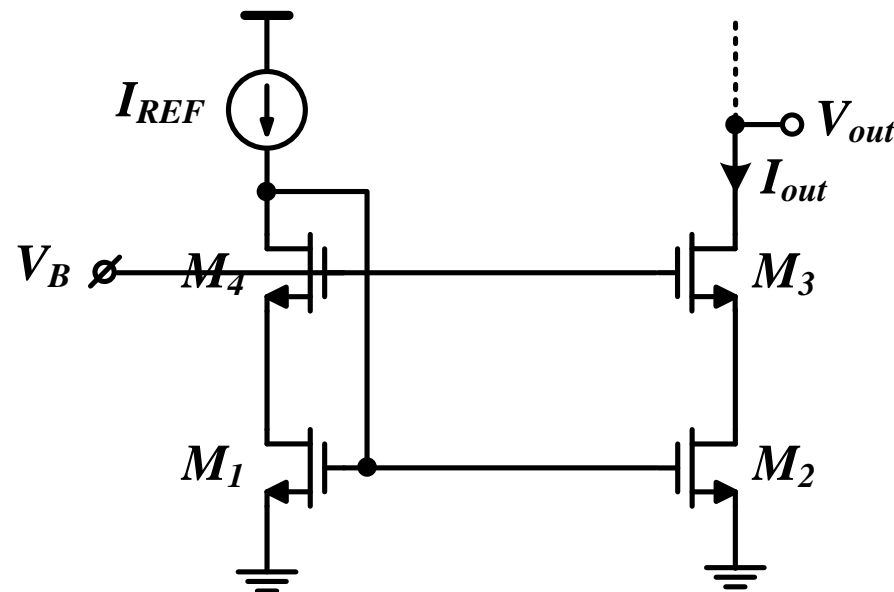
- ❑ We forced $V_{DS2} = V_{DS1} = V_{GS1} = V_{TH} + V_{ov1}$
- ❑ But to remain in saturation we only need $V_{DS2} > V_{ov1}$
- ❑ V_{DS2} has an extra unneeded $V_{TH} \rightarrow$ waste of headroom
- ❑ Solution: Do not set $V_{DS2} = V_{DS1}$
 - Instead, force $V_{DS1} = V_{DS2,min} = V_{ov1} \rightarrow$ wide-swing CM



Wide-swing Cascode CM

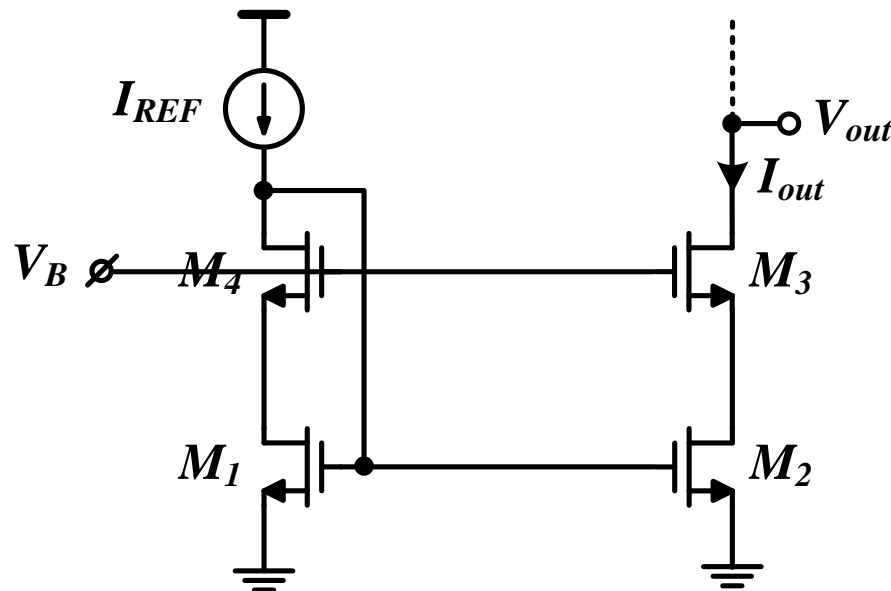
$$V_{TH3,4} + V_{ov3,4} + V_{ov1,2} < \mathbf{V_B} < V_{TH3,4} + V_{TH1,2} + V_{ov1,2}$$

- ❑ As long as V_B is in the valid range, M1-4 will be in sat.
- ❑ The most widely used CM architecture
- ❑ A.k.a. low-voltage current mirror, low-compliance current mirror



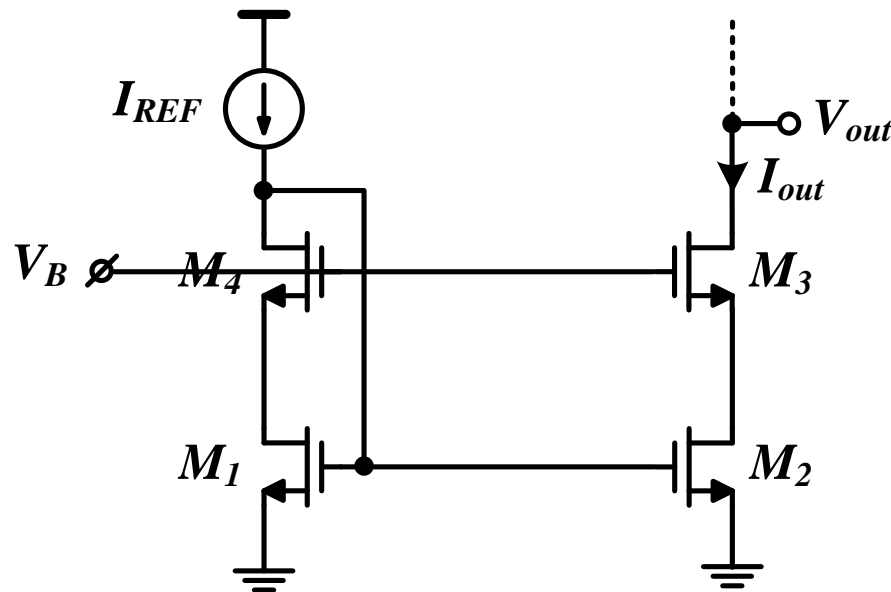
Quiz

- ☐ Compliance range: V_{out} range where the CS behaves as a CS.
- ☐ Assume $V_{TH1,2} = 0.4V$, $V_{TH3,4} = 0.45V$ (body effect), $V_{ov} = 0.1V$.
- ☐ Assume V_B is set $50mV$ above its minimum value.
- ☐ Calculate the CS compliance range.



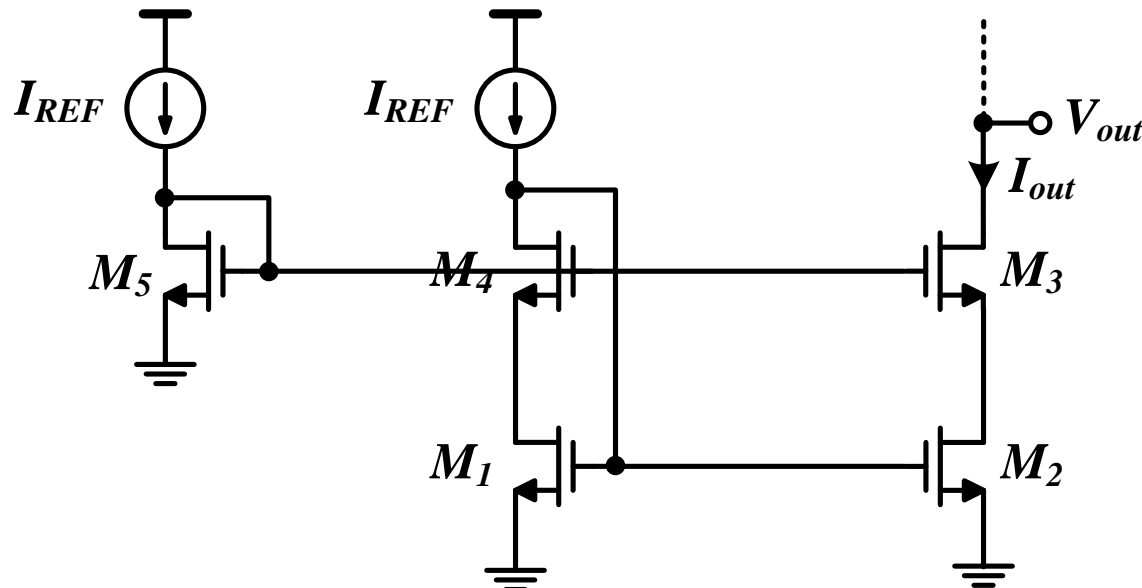
Quiz

- ☐ Compliance range: V_{out} range where the CS behaves as a CS.
- ☐ Assume $V_{TH1,2} = 0.4V$, $V_{TH3,4} = 0.45V$ (body effect), $V_{ov} = 0.1V$.
- ☐ Assume V_B is set $50mV$ above its minimum value.
- ☐ Calculate the CS compliance range.
- ☐ Practically, we don't bias M1-2 at the edge of saturation (why?).
- ☐ What is the magic battery that will generate V_B ?



The Magic Battery

- ❑ To generate voltages we use I -to- V : diode connected transistor
- ❑ Assume M1-M4 have the same W/L : $V_B > V_{TH3,4} + 2V_{ov1-4}$
$$V_{ov5} > 2V_{ov1-4} \rightarrow L_5 > 4L_{1-4}$$
- ❑ Always select $V_B > V_{B,min}$ (e.g., $L_5 \sim 6L_{1-4}$)
 - Need to drive M1 and M2 a bit deeper into saturation
 - Account for body effect of M3 and M4



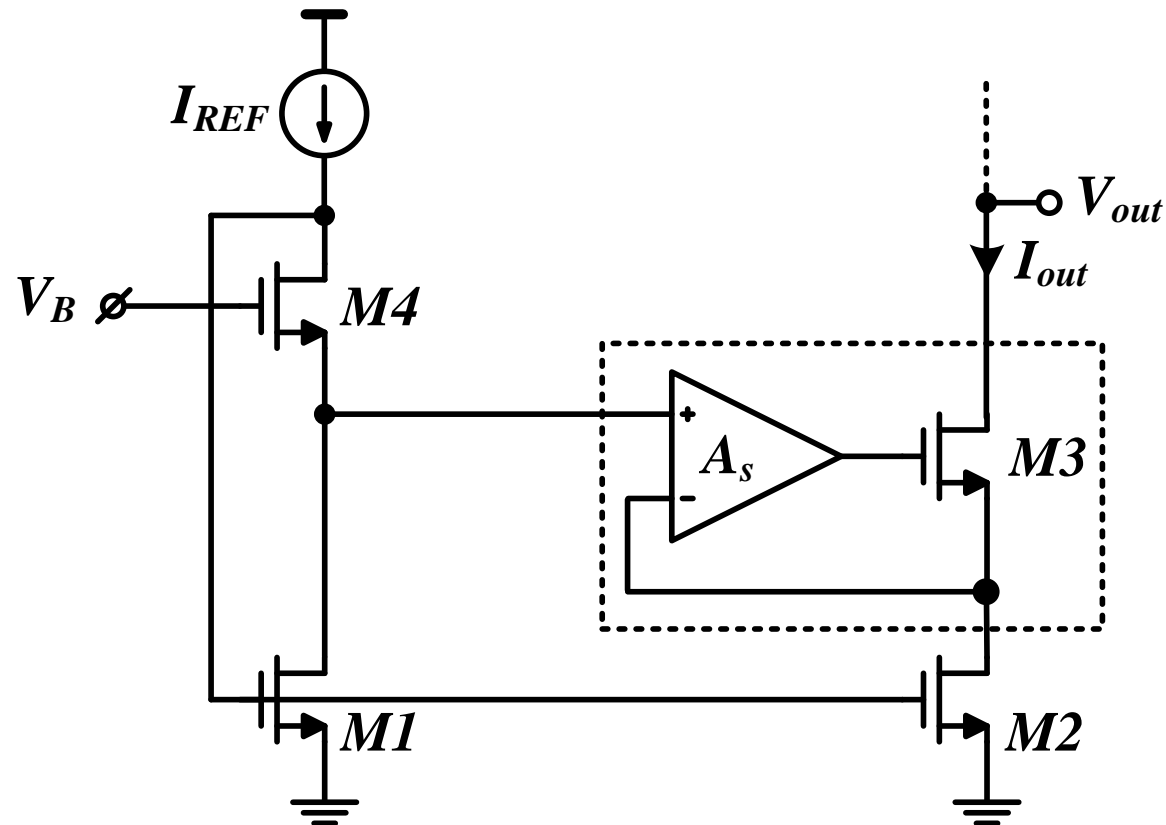
M5 is usually implemented as unit transistors in series

Outline

1. Recapping previous key results
2. Why current source?
3. How to copy (mirror) currents?
4. Cascode current mirror
5. Wide-swing current mirror
6. Super cascode current mirror

Regulated (Super) Cascode CM

- Feedback keeps $V_{DS1} \approx V_{DS2}$ and boosts R_{out}
$$R_{out} \approx r_{o,super}(1 + g_{m,super}R_S) = r_{o3}(A_S g_{m3} r_{o2}) \sim A_S (g_m r_o^2)$$
- Since both V_{GS} and V_{DS} are equal, the mirror works even if M1 and M2 are not in saturation!



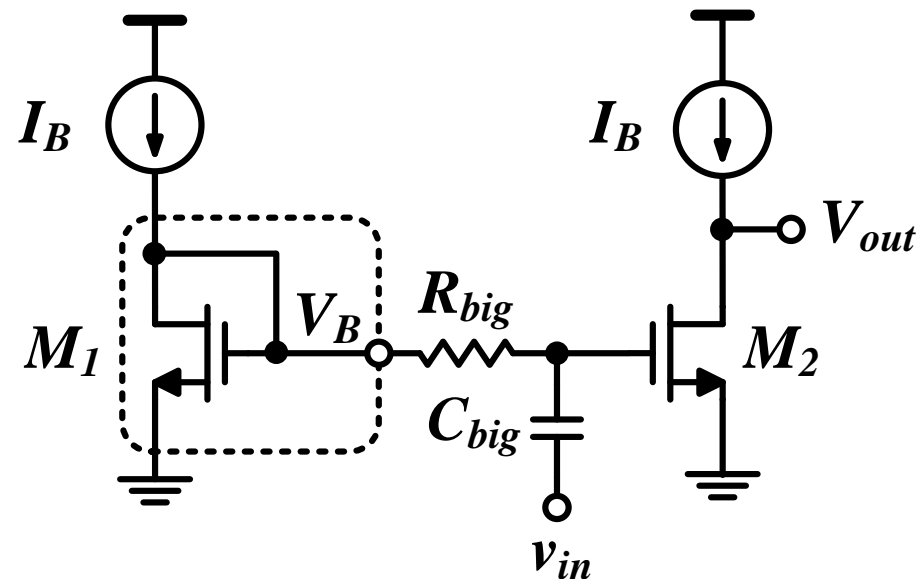
Thank you!

References

- ❑ B. Razavi, “Design Of Analog CMOS Integrated Circuit,” McGraw-Hill, 2nd ed., 2017
- ❑ T. C. Carusone, D. Johns, and K. W. Martin. “Analog Integrated Circuit Design,” Wiley, 2nd ed., 2012
- ❑ R. J. Baker, “CMOS circuit design,” 3rd ed., Wiley, 2010

Replica Biasing

- ❑ To bias the CS amplifier (M2) a replica (M1) is used
- ❑ R_{big} and C_{big} will take a lot of area
 - Only practical for RF circuits (why?)
- ❑ For analog ICs a better trick is used
 - More when we study differential amplifier



Advanced Current Mirrors

- ❑ Can operate with 50mV compliance!
 - Amplifier gain compensate for low R_{out} in triode

